2N4126 TRANSISTOR (PNP)

TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- PNP Silicon Epitaxial Transistor for Switching and Amplifier Applications.
- As Complementary Type, The NPN Transistor 2N4124 is Recommended.

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N4126	TO-92	Bulk	1000pcs/Bag
2N4126-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current -Continuous	-0.2	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	℃ /W
T_J,T_{stg}	Junction Temperature	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.01mA,I_E=0	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-4			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V,I_E=0			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V,I_C=0			-50	nA
DC current gain	$h_{FE(1)}$*	V_{CE}=-1V, I_C=-2mA	120		360	
	$h_{FE(2)}$*	V_{CE}=-1V, I_C=-50mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=-50mA,I_B=-5mA			-0.4	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$*	I_C=-50mA,I_B=-5mA			-0.95	V
Collector output capacitance	C_{ob}	V_{CB}=-5V,I_E=0, f=1MHz			4.5	pF
Transition frequency	f_T	V_{CE}=-20V,I_C=-10mA, f=100MHz	250			MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 1.5%.